

	L #	Hits	Search Text	DBs	Time Stamp
1	L1	7052	(427/508-521,553-559,77,78,226).CCLS.	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2003/08/05 09:07
2	L2	3978	(427/512,515,521,553,556,557,559,77,78,226).CCLS.	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2003/08/05 09:08
3	L3	1471	1 and (short adj wave shortwave "near"adj(infrared IR) NIR ("780" "2500" "1200")adj nm or ("78" "250" "120")adj (angstrom or ".ang."))	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2003/08/05 09:17
4	L4	905	2 and (short adj wave shortwave "near"adj(infrared IR) NIR ("780" "2500" "1200")adj nm or ("78" "250" "120")adj (angstrom or ".ang."))	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2003/08/05 09:14

need space

didn't search whole search is worthless

SNO/020,228

2

	L #	Hits	Search Text	DBs	Time Stamp
5	L5	370	3 and (electrode electrocatalytic\$5 electrocatalysis)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM_ TDB	2003/08/05 09:16
6	L6	244	4 and (electrode electrocatalytic\$5 electrocatalysis)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM_ TDB	2003/08/05 09:16
7	L7	14258	(electrode electrocatalytic\$5 electrocatalysis)same (short adj wave shortwave "near"adj (infrared IR) NIR ("780" "2500" "1200")adj nm or ("78" "250" "120")adj (angstrom or ".ang."))	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM_ TDB	2003/08/05 09:18
8	L8	92	5 and 7	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM_ TDB	2003/08/05 09:18

3

	L #	Hits	Search Text	DBs	Time Stamp
9	L10	28	8 not 9	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2003/08/05 09:19
10	L9	64	6 and 7	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2003/08/05 09:21
11	L11	81	nearinfrared nearIR	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2003/08/05 09:29
12	L12	226	1 and (short adj wave shortwave nearinfrared nearIR ("near" adj(infrared IR)) NIR ("780" "2500" "1200")adj nm or ("78" "250" "120")adj (angstrom or ".ang."))	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2003/08/05 09:36

4

	L #	Hits	Search Text	DBs	Time Stamp
13	L13	226	1 and (short adj wave shortwave nearinfrared nearIR! ("near!" adj(infrared IR)) NIR ("780" "2500" "1200")adj nm or ("78" "250" "120")adj (angstrom or ".ang."))	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2003/08/0 5 09:37
14	L14	226	1 and (short adj wave shortwave nearinfrared nearIR! ("near!" adj(infrared IR)) NIR ("780!" "2500!" "1200!")adj nm or ("78!" "250!" "120!")adj (angstrom or ".ang."))	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2003/08/0 5 09:39
15	L15	226	1 and (short adj wave shortwave nearinfrared nearIR! ("near!" adj(infrared IR)) NIR ("780!" "2500!" "1200!")adj nm or ("78!" "250!" "120!")adj (angstrom or ".ang."))	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2003/08/0 5 09:43
16	L16	128	2 and (short adj wave shortwave nearinfrared nearIR! ("near!" adj(infrared IR)) NIR ("780!" "2500!" "1200!")adj nm or ("78!" "250!" "120!")adj (angstrom or ".ang."))	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2003/08/0 5 09:41

*Wrong
placent*

2

Correct

	L #	Hits	Search Text	DBs	Time Stamp
17	L17	39	15 and (electrode electrocatalytic\$5 electrocatalysis)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2003/08/05 09:42
18	L18	23	16 and (electrode electrocatalytic\$5 electrocatalysis)	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2003/08/05 09:42
19	L19	17	17 and 7	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2003/08/05 09:42
20	L20	1515	(electrode electrocatalytic\$5 electrocatalysis) same (short adj wave shortwave nearinfrared nearIR! ("near"! adj(infrared IR)) NIR ("780"! "2500"! "1200"!)adj nm or ("78"! "250"! "120"!)adj (angstrom or ".ang."))	USPA T; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2003/08/05 09:44

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	L #	Hits	Search Text	DBs	Time Stamp
21	L21	15	17 and 20	USPAT; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2003/08/05 09:44
22	L22	11	18 and 20	USPAT; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2003/08/05 09:45
23	L23	4	21 not 22	USPAT; US-P GPUB ; EPO; JPO; DERW ENT; IBM TDB	2003/08/05 09:45

- L24 (2) JP and "60243280"
- L25 (21) 427/542, CCLS, and (short----"ans.")
- L26 (1) 25 and 20 — have from 223
- L27 (4) 25 and (checkbox and —)
- L28 (3) 27 not (26 22, 23)
- L29 (24) 17 not (22 23, 26, 27)

like L16

	Document ID	Issue Date	Title	Current OR	Inventor
1	US 2002011 4964 A1	20020822	Electrode treatment	428/472	Shimamune, Takayuki et al.
2	US RE37896 E	20021029	Solution for fabrication of electro-n-emitting devices, manufacture method of electro-n-emitting devices, and manufacture method of image-forming apparatus	427/126.1	Tomida, Yoshinori et al.
3	US RE37875 E	20021015	Solid imaging process using component homogenization	264/401	Lawton, John A.
4	US 6000982 A	19991214	Method of manufacturing a cold-cathode for a discharge device	445/51	Nakamura, Osamu et al.

L27

this case →

7

Part C
Size
78 A

NIK not used

D13
D15

reflected to
500-2500nm range
- on 50% and 20%
also use wa lamps

for 1/6 order

(D20)

	Document ID	Issue Date	Title	Current OR	Inventor
5	US 5749763 A	19980512	Display device with electro-n-emitting device with electro-n-emitting region insulated from electrodes	445/51	Yoshioka, Seishiro et al.
6	US 5714391 A	19980203	Method of manufacturing a compound semiconductor thin film for a photoelectric or solar cell device	438/99	Omura, Kuniyoshi et al.
7	US 5116643 A	19920526	Method for preparing PLZT, PZT and PLT sol-gels and fabricating ferroelectric thin films	427/126.3	Miller, William D. et al.

Please check 250A

check 250A of the making

8

	Document ID	Issue Date	Title	Current OR	Inventor
8	(B28) In a pub US 5034246 A	19910723	Method for forming tungsten oxide films	427/126.3	Mance, Andrew M. et al.
9	(D56) UV-vis spect.		Method for preparing plzt, pzt and plt sol-gels and fabricating ferroelectric thin films	427/126.3	Miller, William D. et al.
10	US 4946710 A	19900807	Method for preparing PLZT, PZT and PLT sol-gels and fabricating ferroelectric thin films	427/126.3	Miller, William D. et al.
11	(B6) In the market - photoconductive high sensitive to VIS & NIR light US 4160185 A (D10) A photoconductive	19790703	Red sensitive photocathode having an aluminum oxide barrier layer	313/542	Tomasetti, Charles M. et al.

623

10

~~★ ★~~ (P10) [0054]
 Semi-conduct. layer
 to heat paste (bake-
 mm) w/ VTR
 (810nm)

pull

	Document ID	Issue Date	Title	Current OR	Inventor
1	US 2001000 6722 A1	2001070 5	Substrate having repaired metallic pattern and method and device for repairing metallic pattern on substrate	428/209	Sakai, Osamu et al.
	[0055]	VTR rays			
2	US 6025038 A	2000021 5	Method for depositing rare-earth boride onto a substrate	427/554	Dowben, Peter A. et al.
3	US 3930064 A	1975123 0	Method for curing a coating on a base	427/492	Sander, Conrad
	(B20) Additional secondary glass, approx to 500nm				
4	JP 6024327 9 A	1985120 3	FORMATION OF TRANSPARENT ELECTRODE		TANAKA, TAKAO et al.

(B20) Additional secondary glass, approx to 500nm
 X wing 2

As - UV flash lamp
 (42) Short wave curable 17.1% nm